

FDFME3N311ZT

Integrated N-Channel PowerTrench® MOSFET and Schottky Diode

30 V, 1.6 A, 299 mΩ

Features

- Max $r_{DS(on)}$ = 299 mΩ at $V_{GS} = 4.5$ V, $I_D = 1.6$ A
- Max $r_{DS(on)}$ = 410 mΩ at $V_{GS} = 2.5$ V, $I_D = 1.3$ A
- Low profile: 0.55 mm maximum in the new package MicroFET 1.6x1.6 **Thin**
- Free from halogenated compounds and antimony oxides
- HBM ESD protection level > 1600V (Note3)
- RoHS Compliant



General Description

This device is designed specifically as a single package solution for a boost topology in cellular handset and other ultra-portable applications. It features a MOSFET with low input capacitance, total gate charge and on-state resistance. An independently connected schottky diode with low forward voltage and reverse leakage current to maximize boost efficiency.

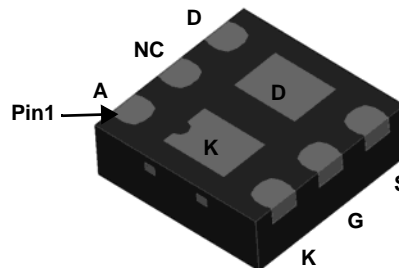
The MicroFET 1.6x1.6 **Thin** package offers exceptional thermal performance for its physical size and is well suited to switching and linear mode applications.

Applications

- Boost Functions

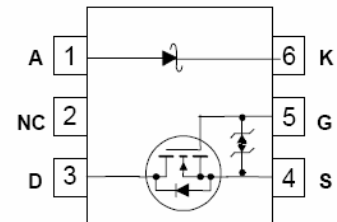


BOTTOM



TOP

MicroFET 1.6x1.6 Thin



MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rated	Units
V_{DS}	Drain to Source Voltage	30	V
V_{GS}	Gate to Source Voltage	± 12	V
I_D	Drain Current -Continuous $T_A = 25^\circ\text{C}$ (Note 1a)	1.6	A
	-Pulsed	4.5	
P_D	Power Dissipation $T_C = 25^\circ\text{C}$	1.1	W
	Power Dissipation $T_A = 25^\circ\text{C}$ (Note 1a)	0.5	
V_{RRM}	Schottky Repetitive Peak Reverse Voltage	28	V
I_O	Schottky Average Forward Current	1	A
T_J, T_{STG}	Operating and Storage Junction Temperature Range (Note 4)	-55 to +150	$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	110	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1b)	234	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1c)	95	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1d)	210	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
1T	FDFME3N311ZT	MicroFET 1.6x1.6 Thin	7"	8mm	5000 units

Electrical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250\text{ }\mu\text{A}$, $V_{GS} = 0\text{ V}$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, referenced to $25\text{ }^\circ\text{C}$		25		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{ V}$, $V_{GS} = 0\text{ V}$			1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 12\text{ V}$, $V_{DS} = 0\text{ V}$			± 10	μA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\text{ }\mu\text{A}$	0.5	1	1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, referenced to $25\text{ }^\circ\text{C}$		-3		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Drain to Source On Resistance	$V_{GS} = 4.5\text{ V}$, $I_D = 1.6\text{ A}$		235	299	m Ω
		$V_{GS} = 2.5\text{ V}$, $I_D = 1.3\text{ A}$		296	410	
		$V_{GS} = 4.5\text{ V}$, $I_D = 1.6\text{ A}$, $T_J = 150\text{ }^\circ\text{C}$		327	420	
g_{FS}	Forward Transconductance	$V_{DS} = 5\text{ V}$, $I_D = 1.6\text{ A}$		2.8		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 15\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$		55	75	pF
C_{oss}	Output Capacitance			15	20	pF
C_{rss}	Reverse Transfer Capacitance			7	10	pF
R_g	Gate Resistance			7.5		Ω

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 15\text{ V}$, $I_D = 1.6\text{ A}$ $V_{GS} = 4.5\text{ V}$, $R_{GEN} = 6\text{ }\Omega$		6	12	ns
t_r	Rise Time			8	16	ns
$t_{d(off)}$	Turn-Off Delay Time			22	35	ns
t_f	Fall Time			1.4	2.8	ns
Q_g	Total Gate Charge		$V_{GS} = 4.5\text{ V}$		1	1.4
Q_{gs}	Gate to Source Gate Charge	$V_{DD} = 15\text{ V}$		0.2		nC
Q_{gd}	Gate to Drain "Miller" Charge	$I_D = 1.6\text{ A}$		0.3		nC

Drain-Source Diode Characteristics

I_S	Maximum continuous Drain-Source Diode Forward Current				1.6	A
V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{ V}$, $I_S = 0.9\text{ A}$ (Note 2)		0.9	1.2	V
t_{rr}	Reverse Recovery Time	$I_F = 1.6\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$		12	22	ns
Q_{rr}	Reverse Recovery Charge			3.1	10	nC

Schottky Diode Characteristics

I_R	Reverse Leakage	$V_R = 28\text{ V}$	$T_J = 25\text{ }^\circ\text{C}$		15	100	μA
			$T_J = 85\text{ }^\circ\text{C}$		0.46	4.7	mA
V_F	Forward Voltage	$I_F = 1\text{ A}$	$T_J = 25\text{ }^\circ\text{C}$		0.47	0.57	V
			$T_J = 85\text{ }^\circ\text{C}$		0.45		
V_F	Forward Voltage	$I_F = 500\text{ mA}$	$T_J = 25\text{ }^\circ\text{C}$		0.38	0.48	V
			$T_J = 85\text{ }^\circ\text{C}$		0.33		

Electrical Characteristics

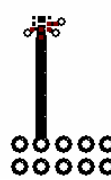
Notes:

1. $R_{\theta JA}$ is determined with the device mounted on a 1 in² oz. copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user's board design.

- (a) MOSFET $R_{\theta JA} = 110$ °C/W when mounted on a 1 in² pad of 2 oz copper, 1.5 " x 1.5 " x 0.062 " thick PCB.
- (b) MOSFET $R_{\theta JA} = 234$ °C/W when mounted on a minimum pad of 2 oz copper. For single operation.
- (c) Schottky $R_{\theta JA} = 95$ °C/W when mounted on a 1 in² pad of 2 oz copper, 1.5 " x 1.5 " x 0.062" thick PCB.
- (d) Schottky $R_{\theta JA} = 210$ °C/W when mounted on a minimum pad of 2 oz copper. For dual operation.



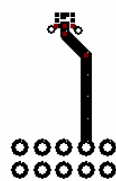
a. 110 °C/W when mounted on a 1 in² pad of 2 oz copper.



b. 234 °C/W when mounted on a minimum pad of 2 oz copper.



c. 95 °C/W when mounted on a 1 in² pad of 2 oz copper.



d. 210 °C/W when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width < 300µs, Duty cycle < 2.0%.

3. The diode connected between the gate and source serves only as protection ESD. No gate overvoltage rating is implied.

4. Rating is applicable to MOSFET only.

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

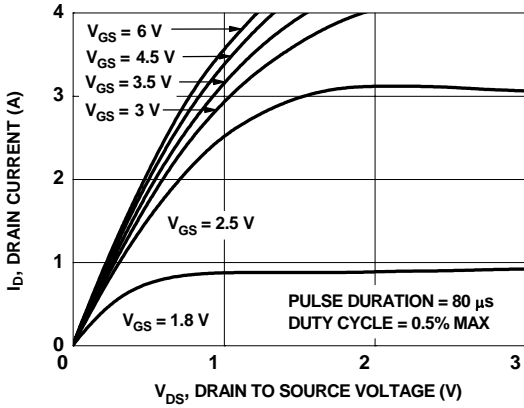


Figure 1. On Region Characteristics

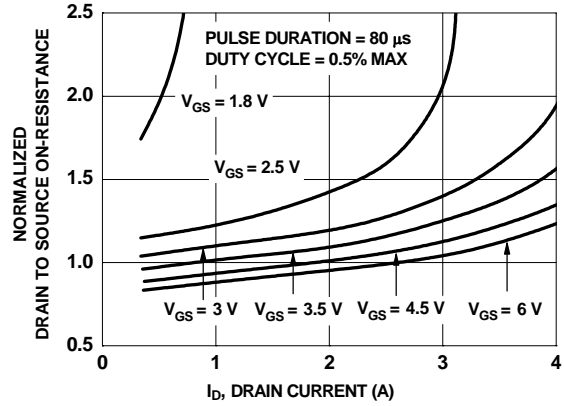


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

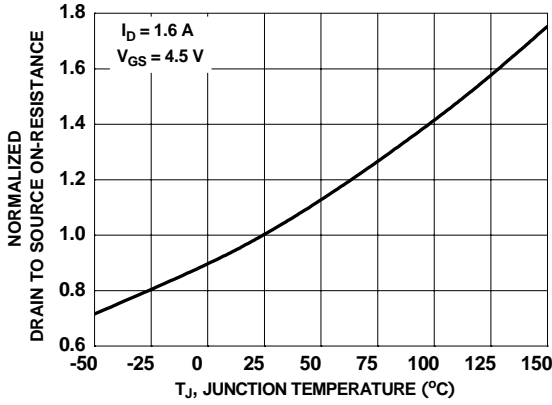


Figure 3. Normalized On Resistance vs Junction Temperature

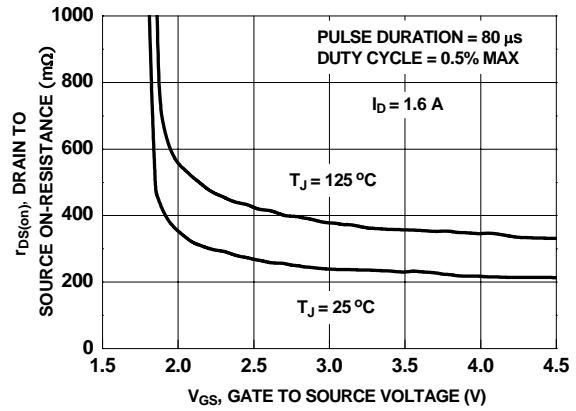


Figure 4. On-Resistance vs Gate to Source Voltage

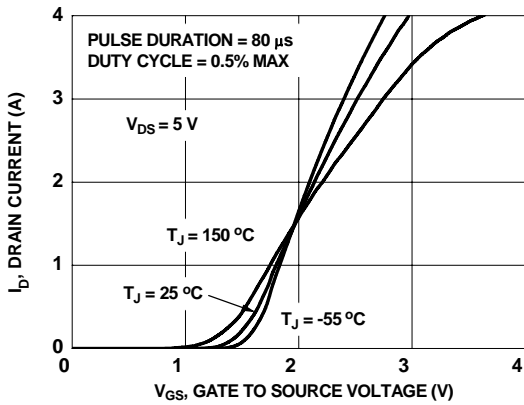


Figure 5. Transfer Characteristics

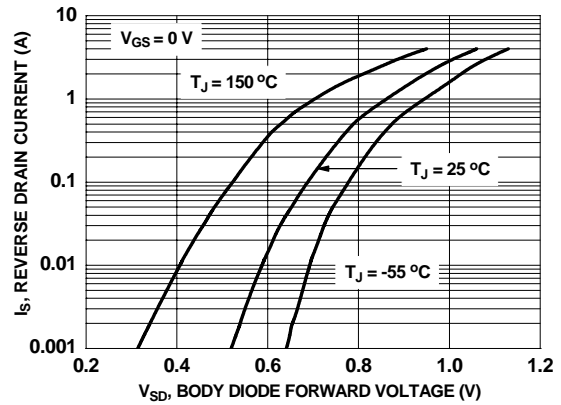


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

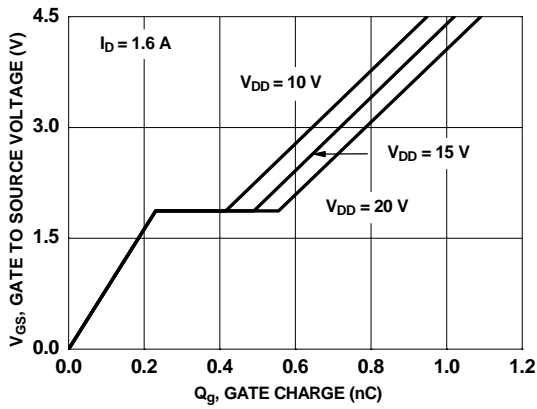


Figure 7. Gate Charge Characteristics

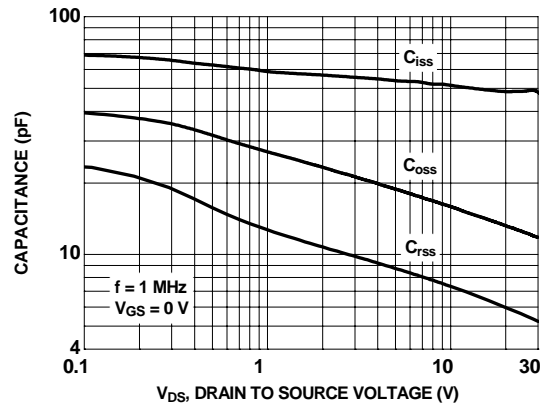


Figure 8. Capacitance vs Drain to Source Voltage

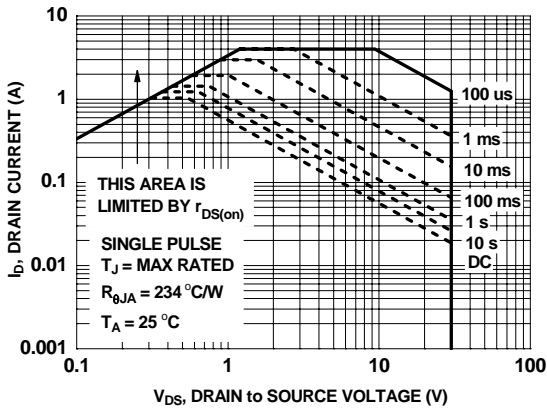


Figure 9. Forward Bias Safe Operating Area

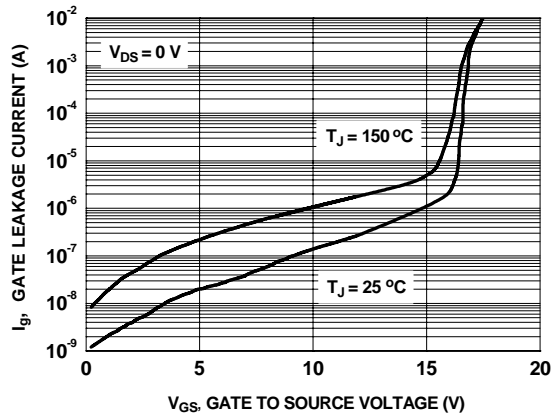


Figure 10. Gate Leakage Current vs Gate to Source Voltage

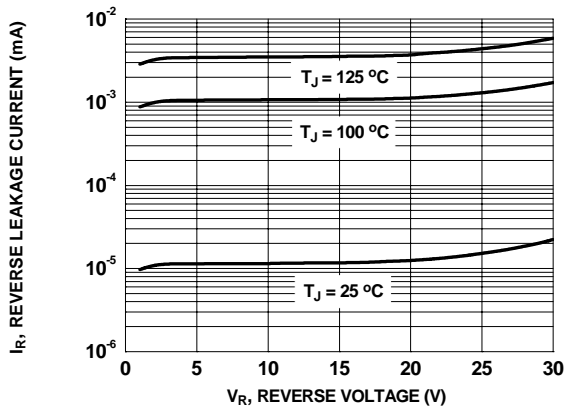


Figure 11. Schottky Diode Reverse Current

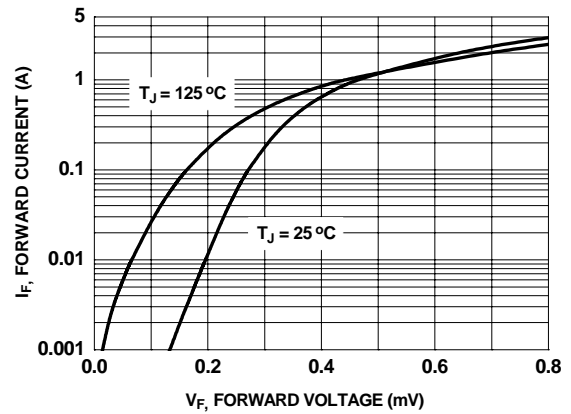


Figure 12. Schottky Diode Forward Voltage

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

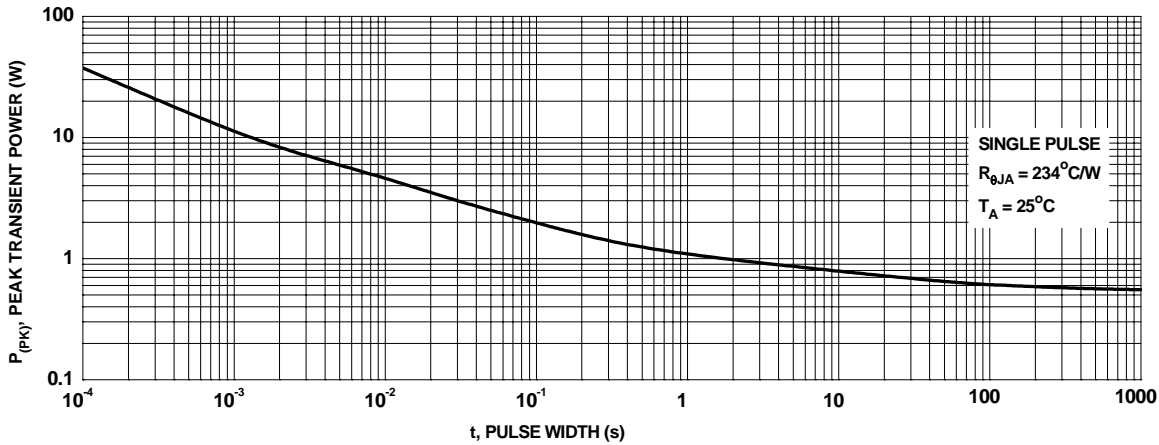


Figure 13. Single Pulse Maximum Power Dissipation

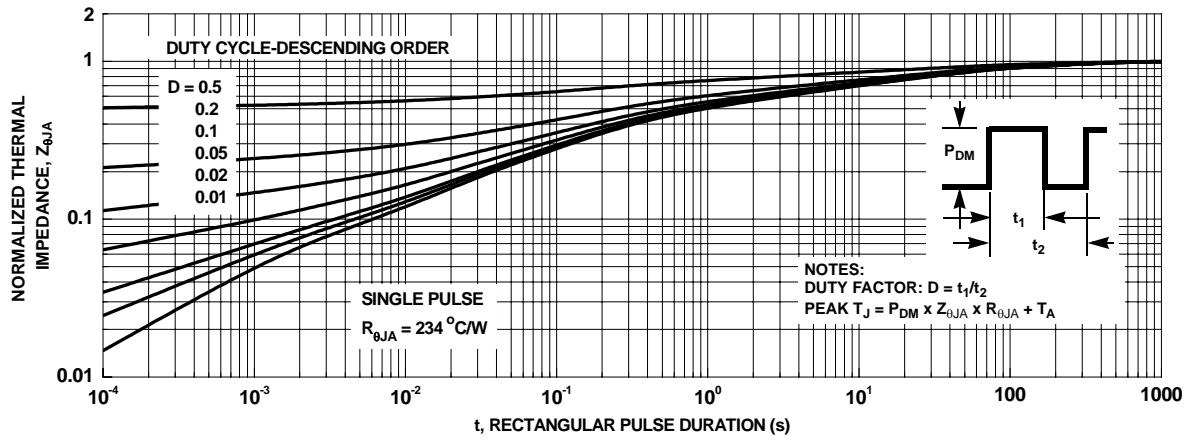
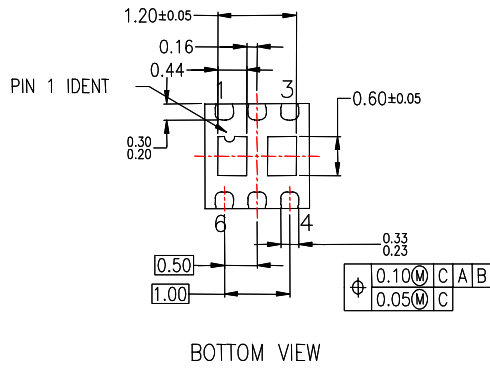
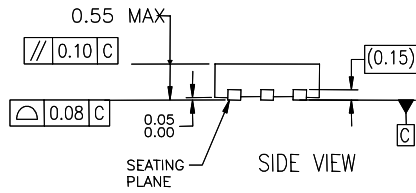
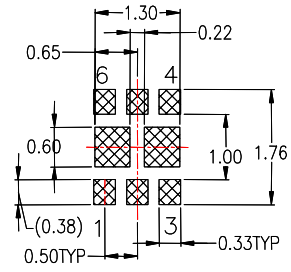
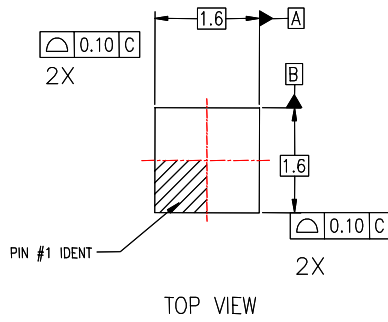


Figure 14. Junction-to-Ambient Transient Thermal Response Curve




Dimensional Outline and Pad Layout





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